

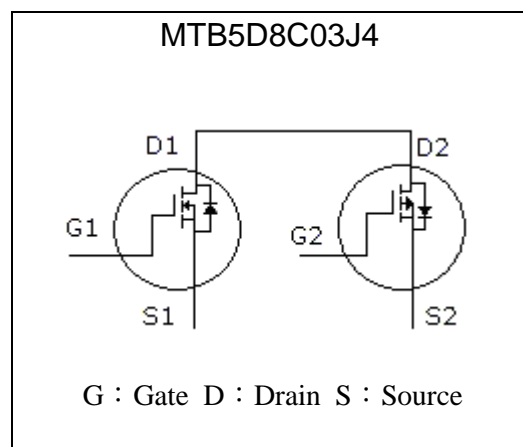
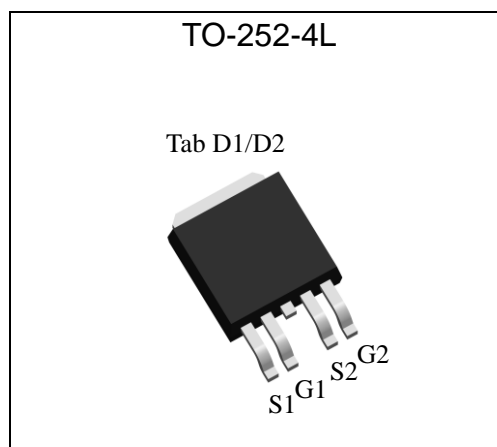
N & P-Channel Enhancement Mode Power MOSFET

MTB5D8C03J4

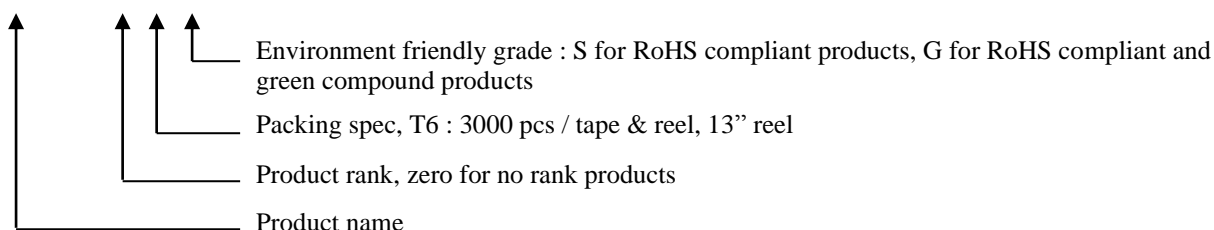
Features

- Low Gate Charge
- Simple Drive Requirement
- RoHS compliant & Halogen-free package

	N-CH	P-CH
BV_{DSS}	30V	-30V
$I_D @ T_C=25^\circ C V_{GS}=10V(-10V)$ (silicon limit)	43A	-30A
$I_D @ T_C=25^\circ C V_{GS}=10V(-10V)$ (package limit)	20A	-20A
$I_D @ T_A=25^\circ C V_{GS}=10V(-10V)$	14.6A	-9.2A
$R_{DS(on)(typ.)} @ V_{GS}=(-)10V$	6.7 m Ω	14 m Ω
$R_{DS(on)(typ.)} @ V_{GS}=(-)4.5V$	11 m Ω	20 m Ω

Equivalent Circuit

Outline

Ordering Information

Device	Package	Shipping
MTB5D8C03J4-0-T6-G	TO-252-4L (RoHS compliant & Halogen-free package)	3000 pcs / Tape & Reel



**Absolute Maximum Ratings** ($T_A=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Limits		Unit
		N-channel	P-channel	
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 20	± 20	
Continuous Drain Current @ $T_C=25^{\circ}\text{C}$, $V_{GS}=10\text{V}(-10\text{V})$ (silicon limit) (Note1)	I_D	43	-30	A
Continuous Drain Current @ $T_C=25^{\circ}\text{C}$, $V_{GS}=10\text{V}(-10\text{V})$ (package limit) (Note1)		20	-20	
Continuous Drain Current @ $T_C=100^{\circ}\text{C}$, $V_{GS}=10\text{V}(-10\text{V})$ (Note1)		27.2	-19	
Continuous Drain Current @ $T_A=25^{\circ}\text{C}$, $V_{GS}=10\text{V}(-10\text{V})$ (Note4)		14.6	-9.2	
Continuous Drain Current @ $T_A=70^{\circ}\text{C}$, $V_{GS}=10\text{V}(-10\text{V})$ (Note4)		11.7	-7.4	
Pulsed Drain Current (Note3)	I_{DM}	80	-80	
Single Pulse Avalanche Current @ $L=0.1\text{mH}$	I_{AS}	15	-20	
Single Pulse Avalanche Energy @ $L=0.5\text{mH}$	E_{AS}	16	-30	mJ
Total Power Dissipation ($T_C=25^{\circ}\text{C}$) (Note1)	P_D	31		W
Total Power Dissipation ($T_C=100^{\circ}\text{C}$) (Note1)		12.4		
Total Power Dissipation ($T_A=25^{\circ}\text{C}$) (Note2)	P_{DSM}	2.9		
Total Power Dissipation ($T_A=70^{\circ}\text{C}$) (Note2)		1.8		
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-55~+150		$^{\circ}\text{C}$

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{\theta JC}$	5	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-ambient, max (Note2)	$R_{\theta JA}$	43	

- Note : 1. The power dissipation P_D is based on $T_{J(MAX)}=150^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2 oz. copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design.
3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^{\circ}\text{C}$. Ratings are based on low frequency and low duty cycles to keep initial $T_J=25^{\circ}\text{C}$.
4. When mounted on the minimum pad size recommended (PCB mount), $t \leq 10\text{s}$.



N-CH Characteristics (Tc=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	30	-	-	V	V _{GS} =0V, I _D =250μA
V _{GS(th)}	1.0	-	2.5		V _{DS} =V _{GS} , I _D =250μA
I _{GSS}	-	-	±100	nA	V _{GS} =±20V, V _{DS} =0V
I _{DSS}	-	-	1	μA	V _{DS} =24V, V _{GS} =0V
	-	-	5		V _{DS} =24V, V _{GS} =0V, T _j =55°C
R _{DS(ON)} *1	-	6.7	8.7	mΩ	V _{GS} =10V, I _D =10A
	-	11	15.5		V _{GS} =4.5V, I _D =7A
G _{FS} *1	-	10.2	-	S	V _{DS} =10V, I _D =7A
Dynamic					
Q _g *1	-	14	-	nC	V _{DS} =15V, I _D =10A, V _{GS} =10V
Q _{gs} *1	-	3	-		
Q _{gd} *1	-	3	-		
t _{d(ON)} *1	-	10	-	ns	V _{DS} =15V, I _D =10A, V _{GS} =10V, R _G =1Ω
t _r *1	-	14	-		
t _{d(OFF)} *1	-	25	-		
t _f *1	-	5	-		
C _{iss}	-	770	-	pF	V _{DS} =25V, V _{GS} =0V, f=1MHz
C _{oss}	-	410	-		
C _{rss}	-	35	-		
R _g	-	0.75	-	Ω	f=1MHz
Source-Drain Diode					
I _S *1	-	-	15	A	
I _{SM} *2	-	-	60		
V _{SD} *1	-	0.86	1.2	V	I _S =10A, V _{GS} =0V
t _{rr} *1	-	19	-	ns	I _F =10A, V _{GS} =0V, dI _F /dt=100A/μs
Q _{rr} *1	-	7	-	nC	

Note : *1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

*2.Pulse width limited by maximum junction temperature.

P-CH Characteristics (Tc=25°C, unless otherwise specified)

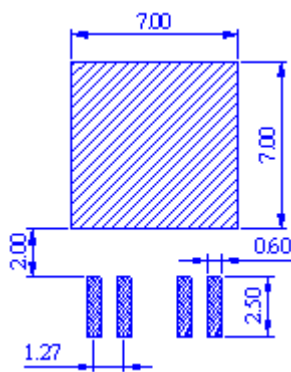
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	-30	-	-	V	V _{GS} =0V, I _D =-250μA
V _{GS(th)}	-1.0	-	-2.5		V _{DS} =V _{GS} , I _D =-250μA
I _{GSS}	-	-	±100	nA	V _{GS} =±20V, V _{DS} =0V
I _{DSS}	-	-	-1	μA	V _{DS} =-24V, V _{GS} =0V
	-	-	-5		V _{DS} =-24V, V _{GS} =0V, T _j =55°C
R _{DS(ON)} *1	-	14	18	mΩ	V _{GS} =-10V, I _D =-10A
	-	20	28		V _{GS} =-5V, I _D =-7A
G _{FS} *1	-	11.2	-	S	V _{DS} =-10V, I _D =-7A

Dynamic					
Qg *1	-	11	-	nC	V _{DS} =-15V, I _D =-10A, V _{GS} =-10V
Qgs *1	-	3	-		
Qgd *1	-	5	-		
t _{d(ON)} *1	-	12	-	ns	V _{DS} =-15V, I _D =-10A, V _{GS} =-10V, R _G =1 Ω
t _r *1	-	19	-		
t _{d(OFF)} *1	-	60	-		
t _f *1	-	11	-		
C _{iss}	-	1600	-	pF	V _{DS} =-25V, V _{GS} =0V, f=1MHz
C _{oss}	-	170	-		
C _{rss}	-	160	-		
R _g	-	5	-	Ω	f=1MHz
Source-Drain Diode					
I _S *1	-	-	-9	A	
I _{SM} *2	-	-	-36		
V _{SD} *1	-	-0.89	-1.2	V	I _S =-10A, V _{GS} =0V
t _{rr} *1	-	13	-	ns	I _F =-10A, V _{GS} =0V, dI _F /dt=100A/μs
Q _{rr} *1	-	7	-	nC	

Note : *1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

*2.Pulse width limited by maximum junction temperature.

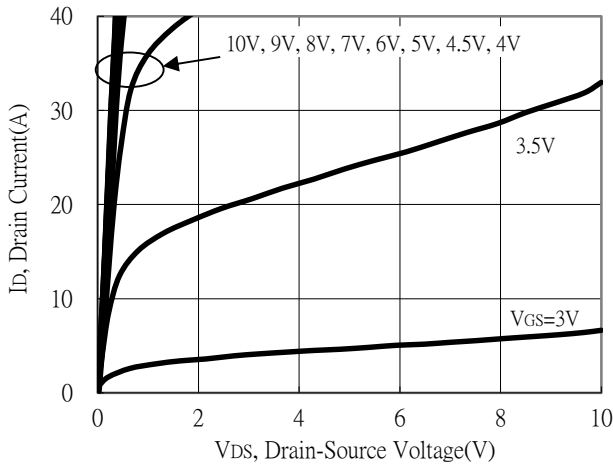
Recommended soldering footprint



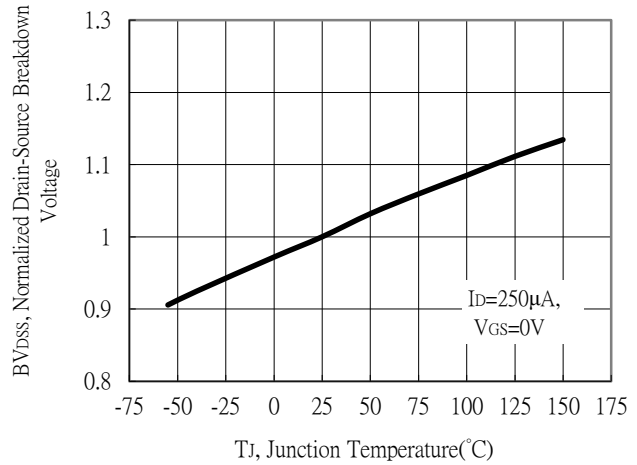
Unit : mm

Q1, N-CH Typical Characteristics

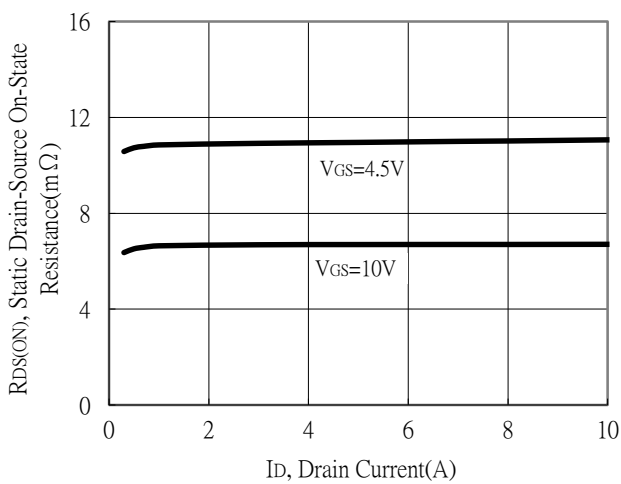
Typical Output Characteristics



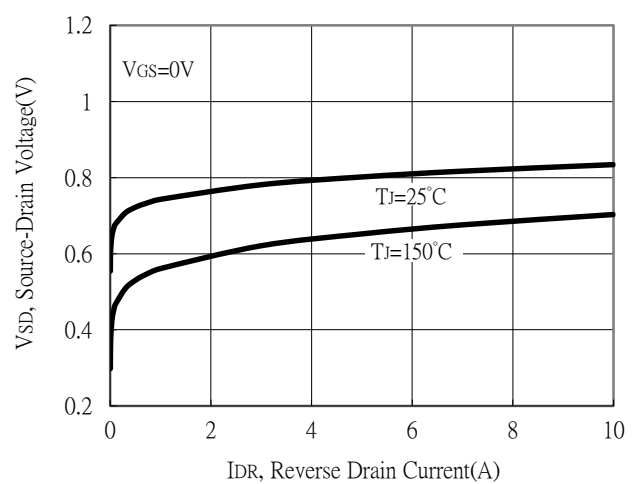
Brekdown Voltage vs Ambient Temperature



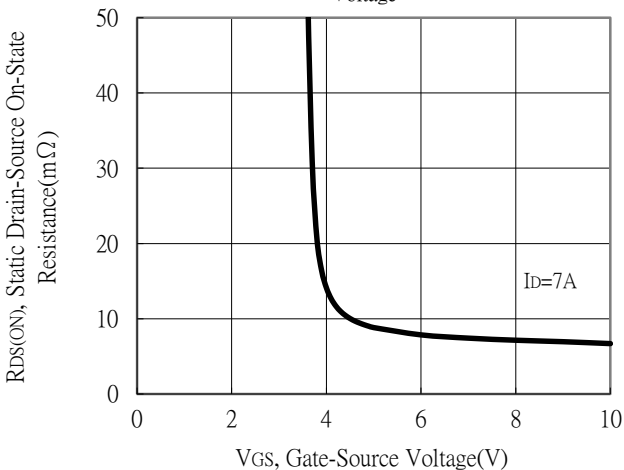
Static Drain-Source On-State resistance vs Drain Current



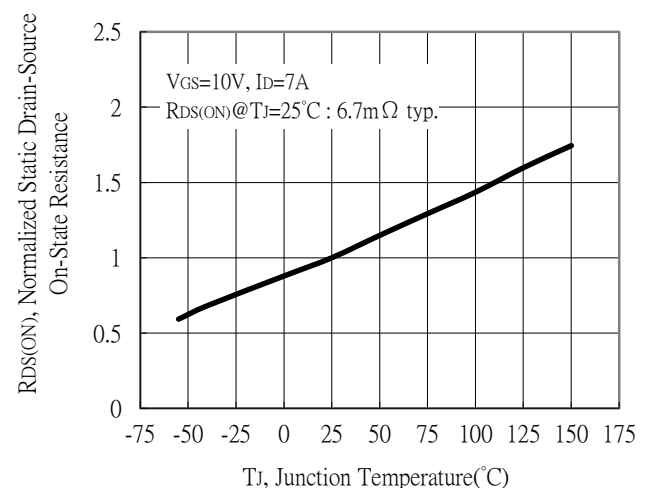
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

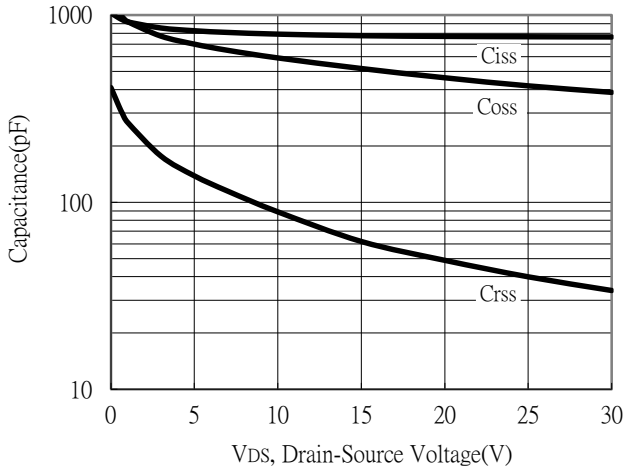


Drain-Source On-State Resistance vs Junction Temperature

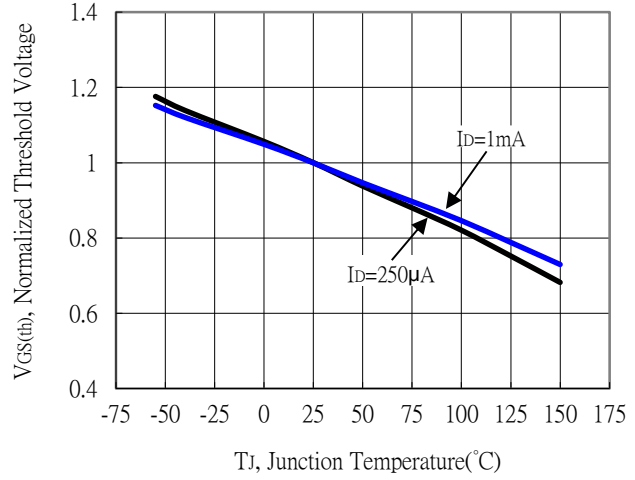


Q1, N-CH Typical Characteristics(Cont.)

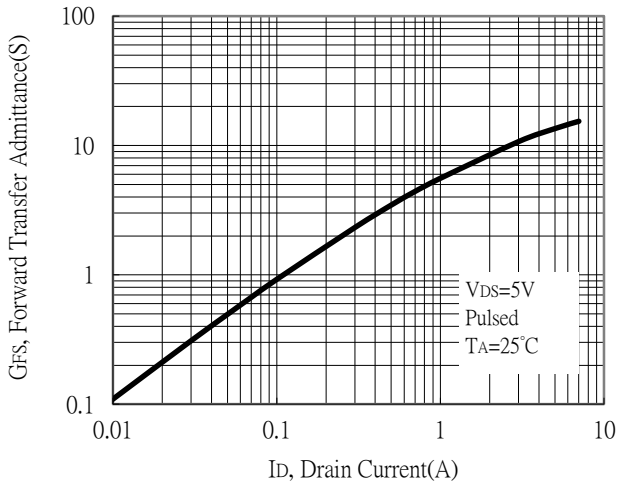
Capacitance vs Drain-to-Source Voltage



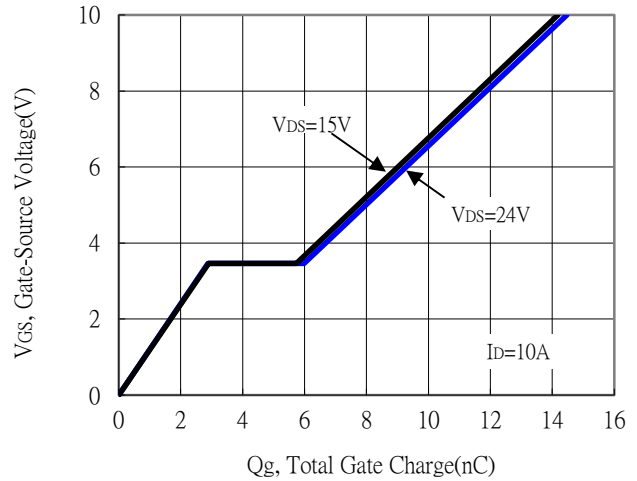
Threshold Voltage vs Junction Temperature



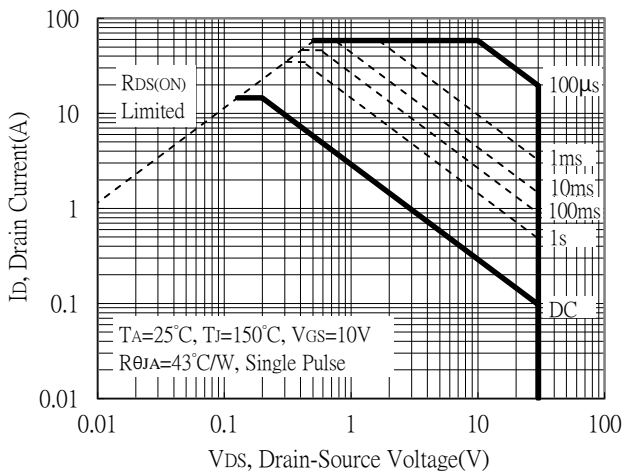
Forward Transfer Admittance vs Drain Current



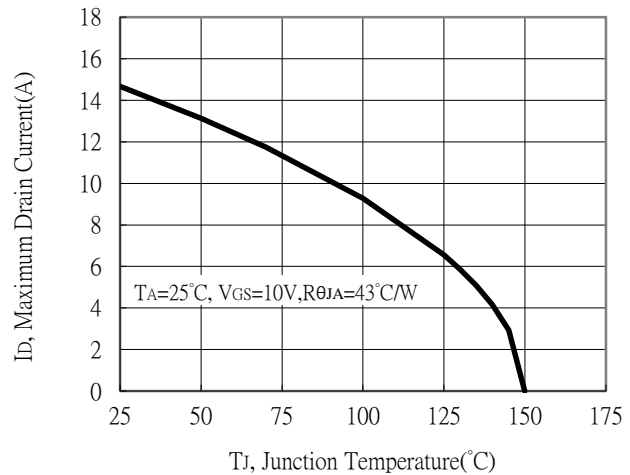
Gate Charge Characteristics



Maximum Safe Operating Area

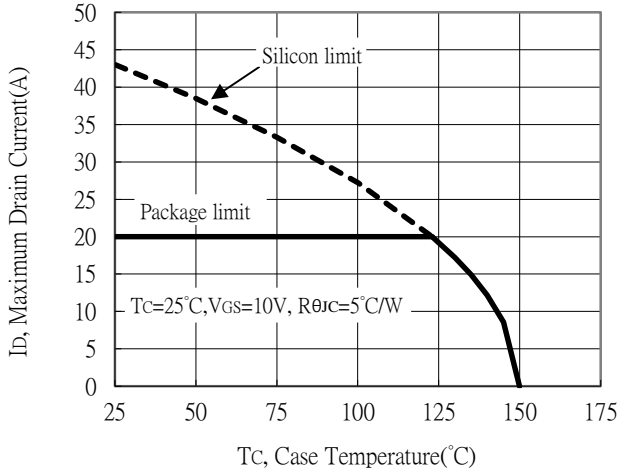


Maximum Drain Current vs Junction Temperature



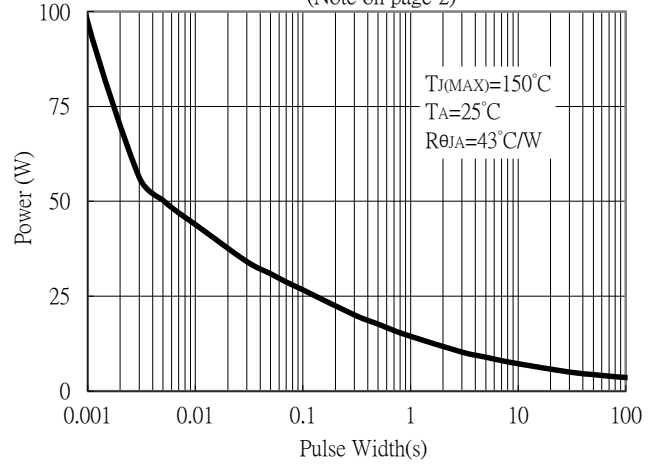
Q1, N-CH Typical Characteristics(Cont.)

Maximum Drain Current vs Case Temperature

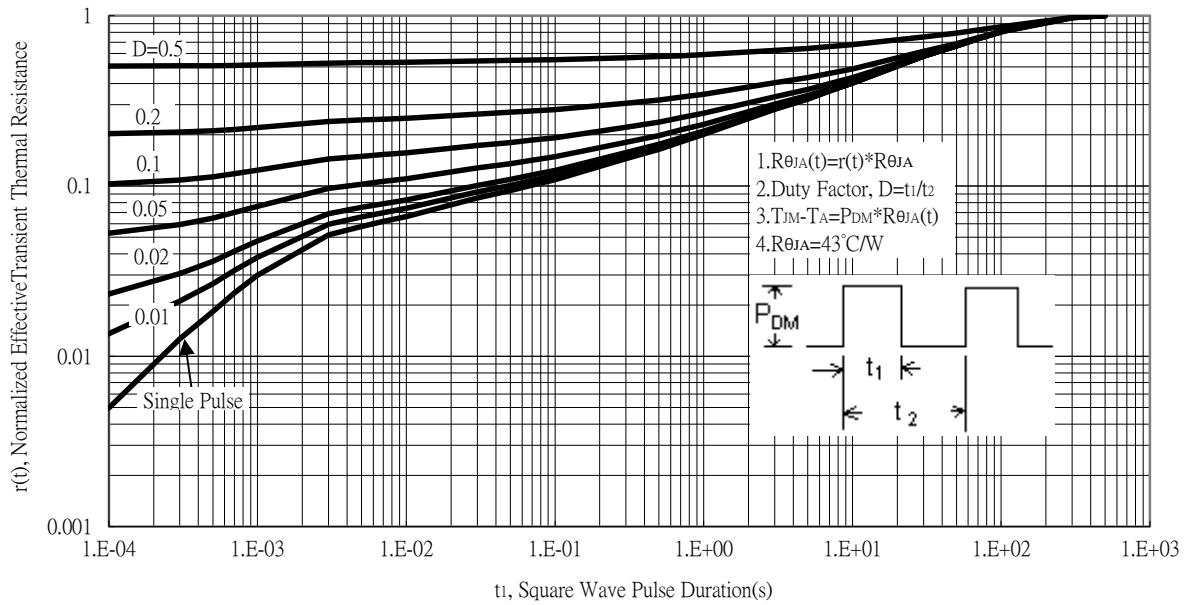


Single Pulse Power Rating, Junction to Ambient

(Note on page 2)

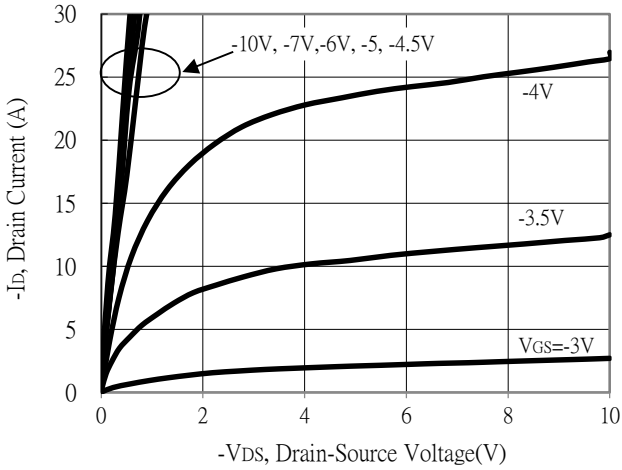


Transient Thermal Response Curves

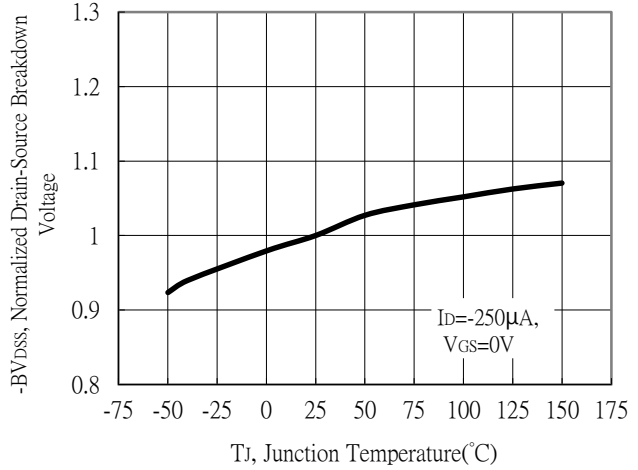


Q2, P-CH Typical Characteristics

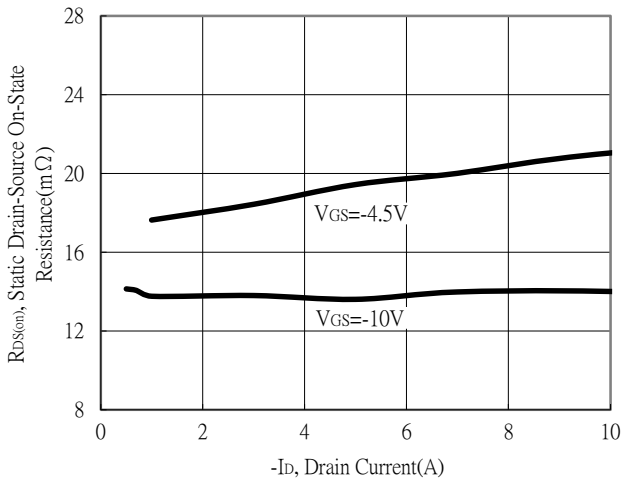
Typical Output Characteristics



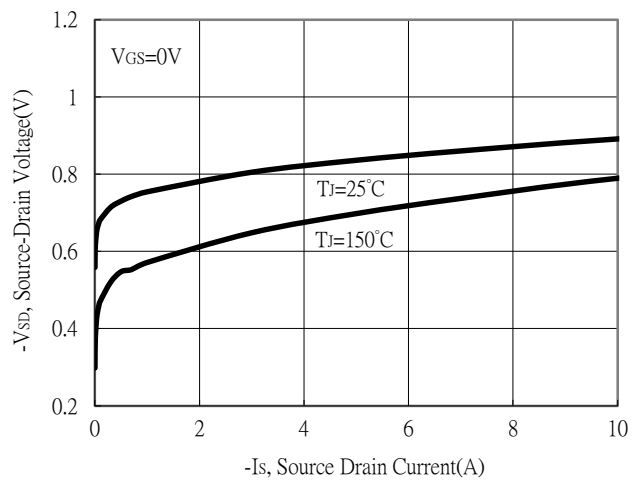
Breakdown Voltage vs Ambient Temperature



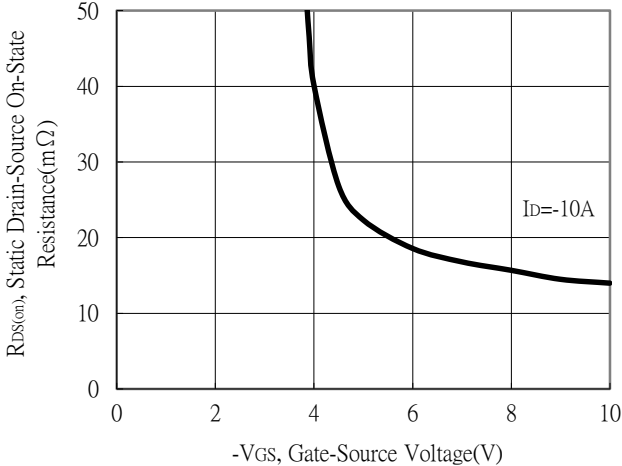
Static Drain-Source On-State resistance vs Drain Current



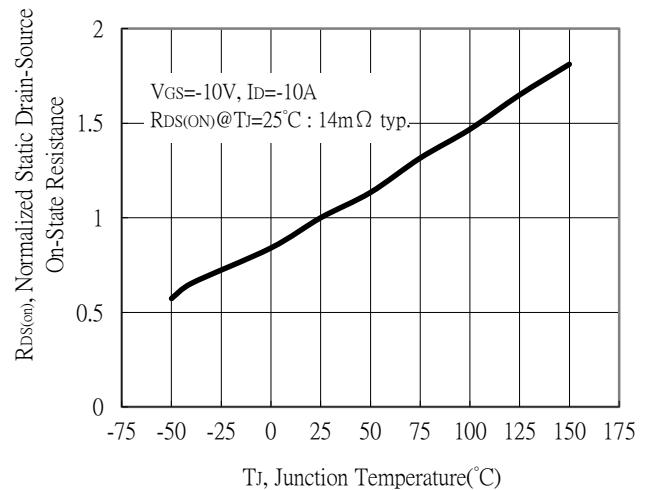
Source Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

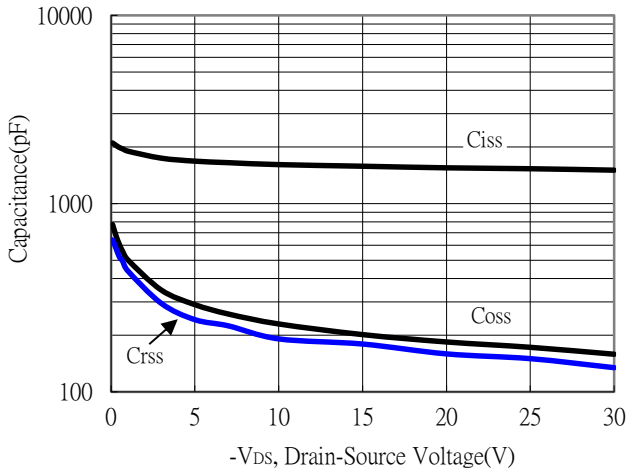


Drain-Source On-State Resistance vs Junction Temperature

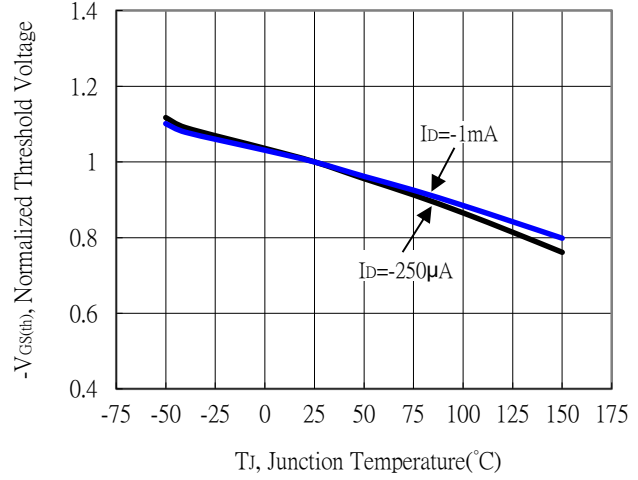


Q2, P-CH Typical Characteristics(Cont.)

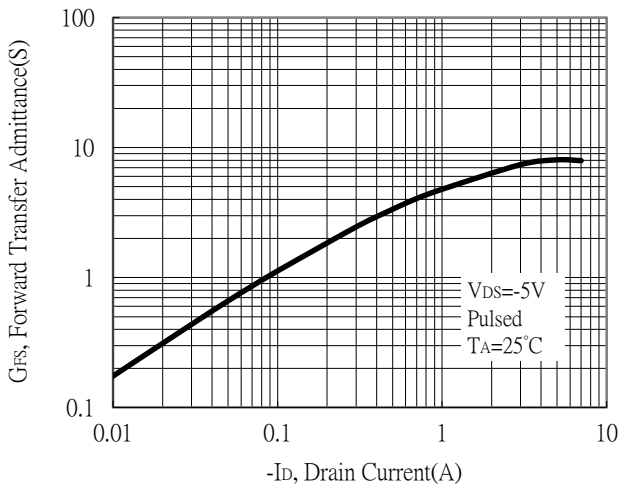
Capacitance vs Drain-to-Source Voltage



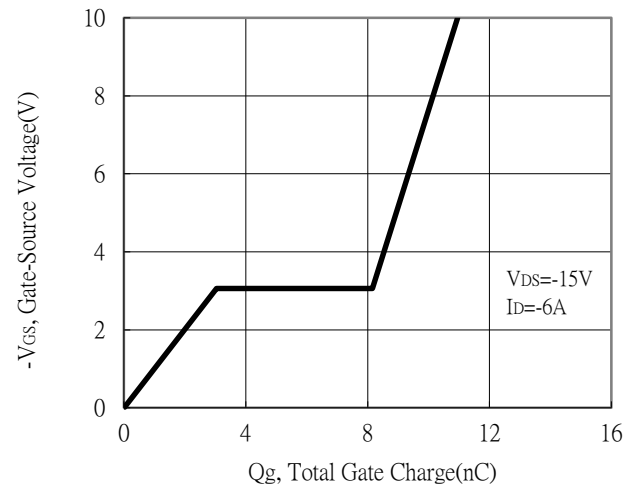
Threshold Voltage vs Junction Temperature



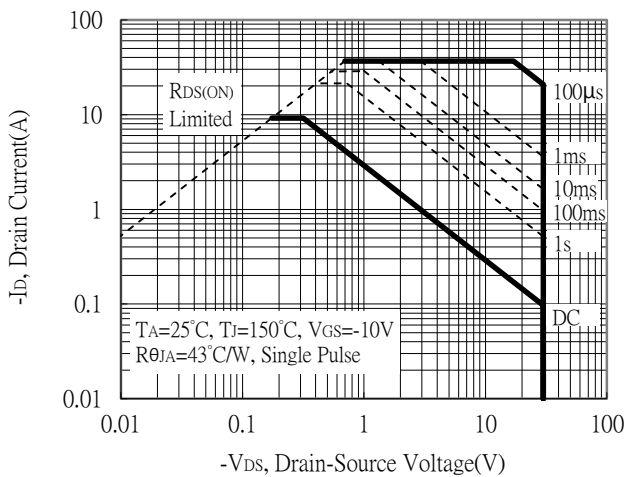
Forward Transfer Admittance vs Drain Current



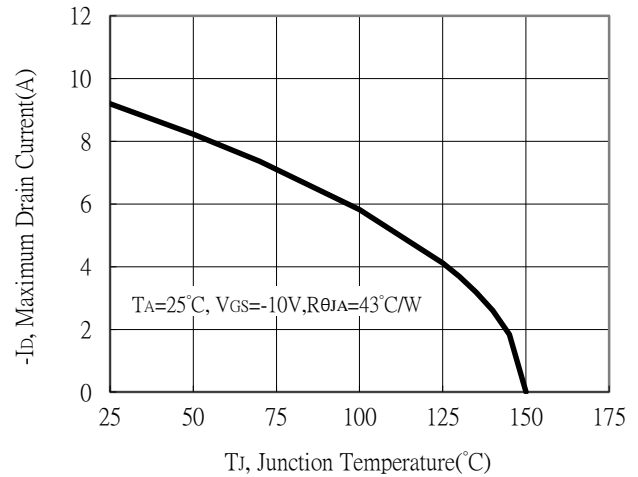
Gate Charge Characteristics



Maximum Safe Operating Area



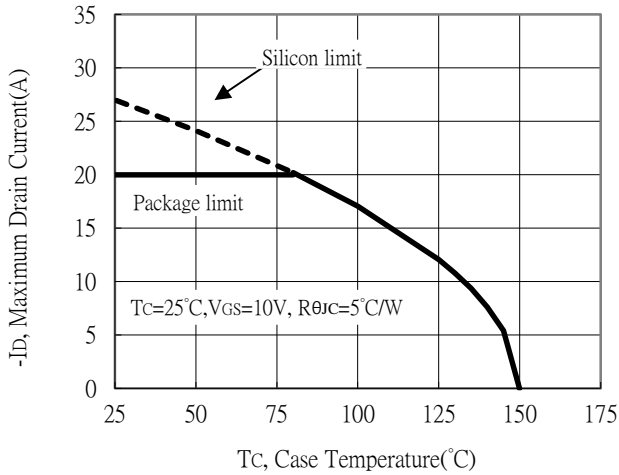
Maximum Drain Current vs Junction Temperature



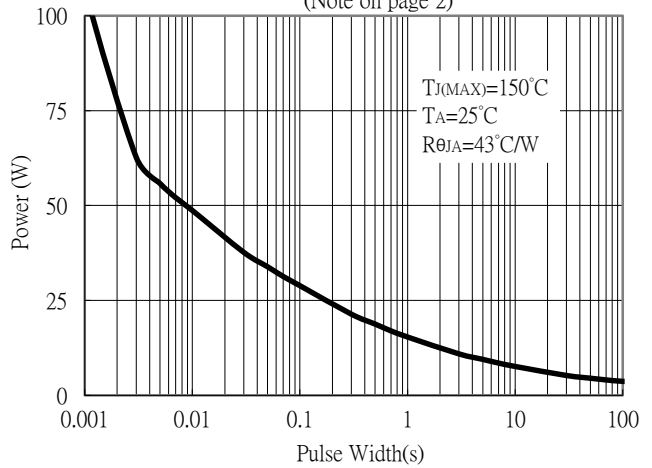


Q2, P-CH Typical Characteristics(Cont.)

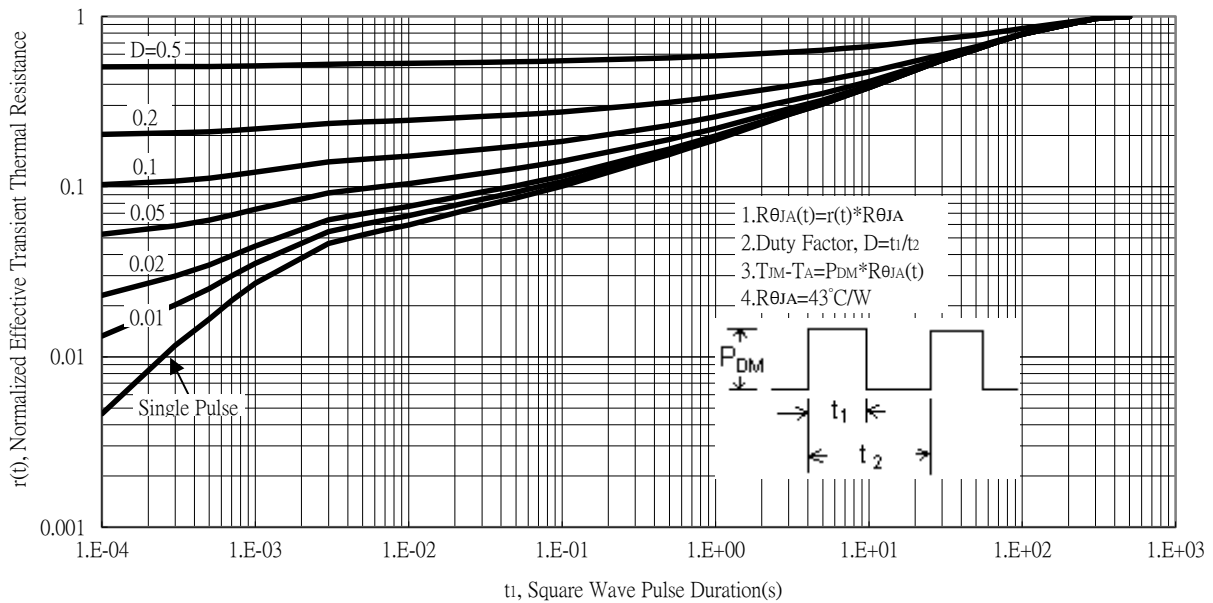
Maximum Drain Current vs Case Temperature



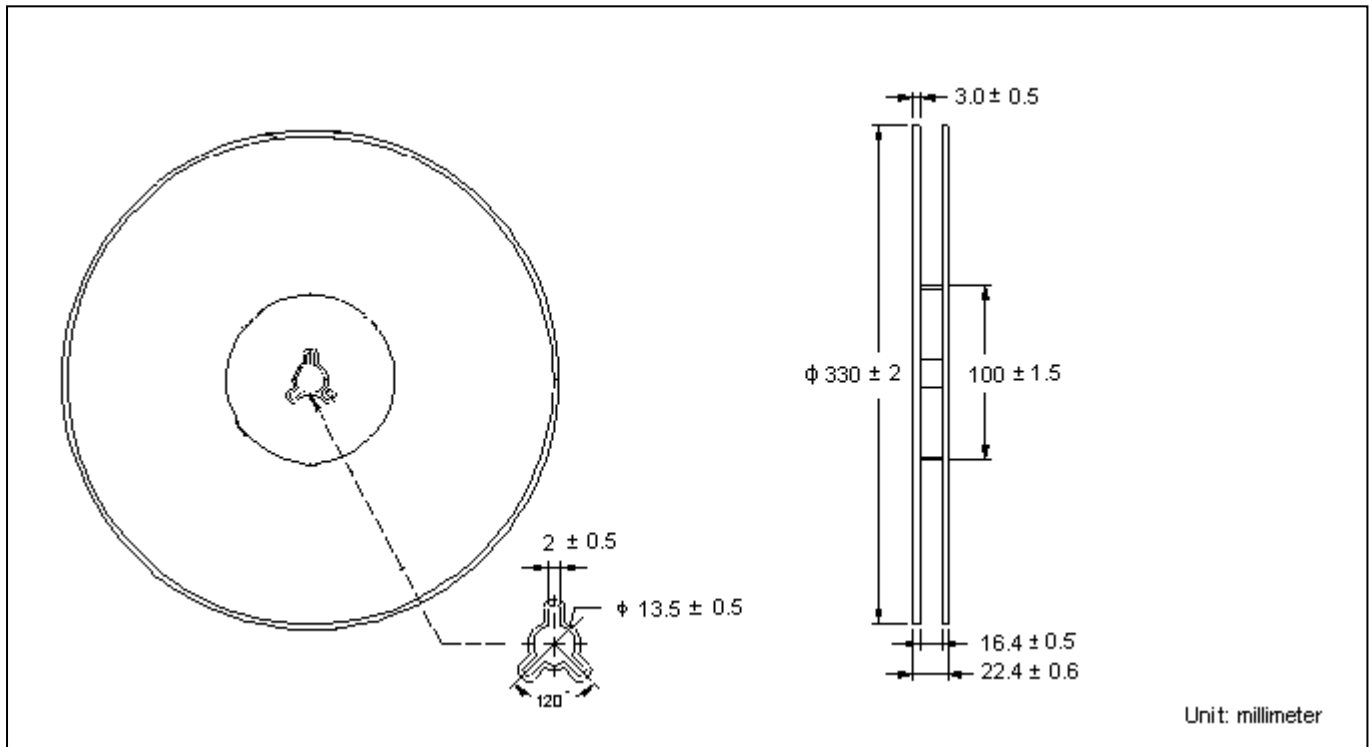
Single Pulse Power Rating, Junction to Ambient
 (Note on page 2)



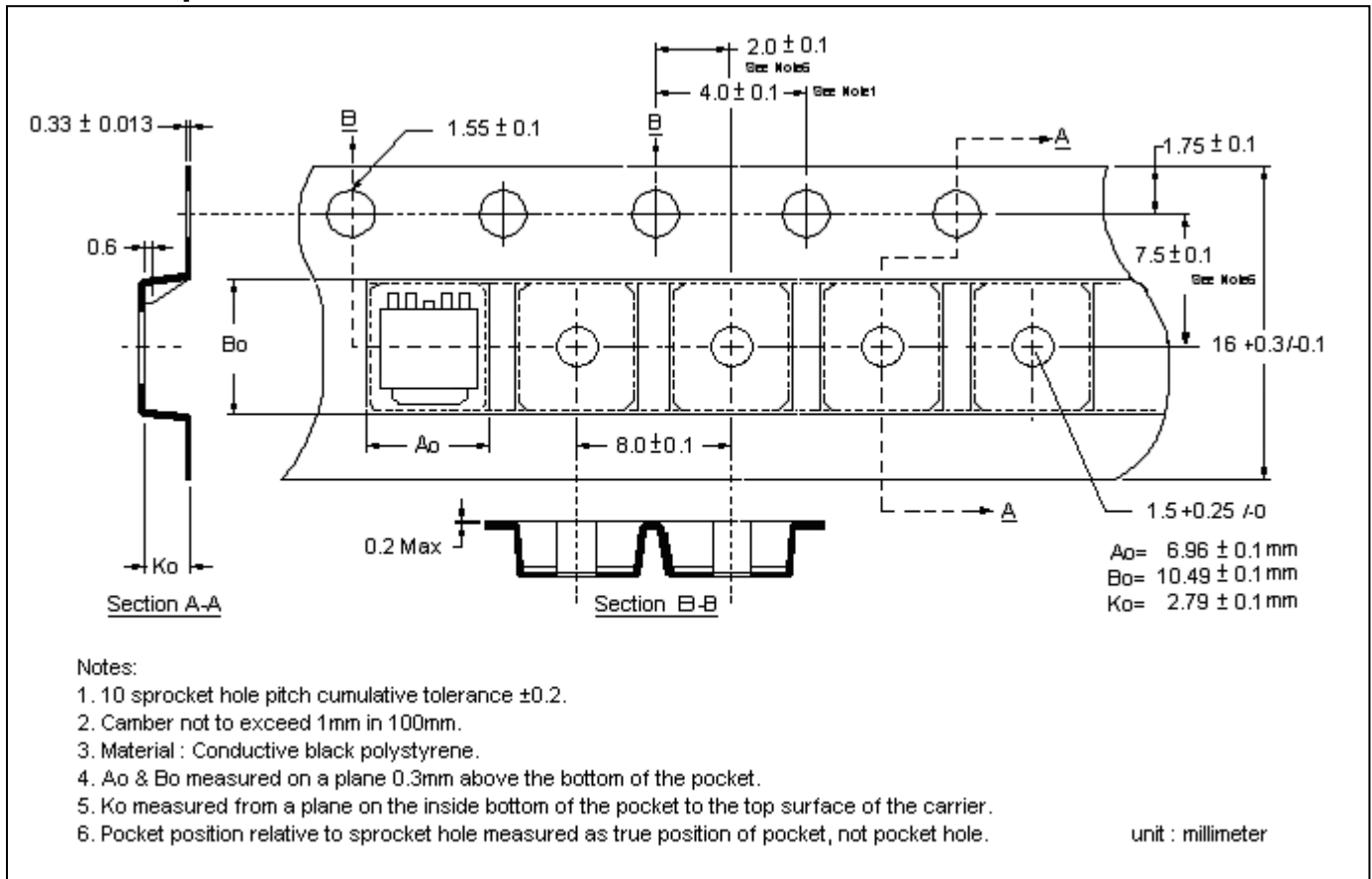
Transient Thermal Response Curves



Reel Dimension



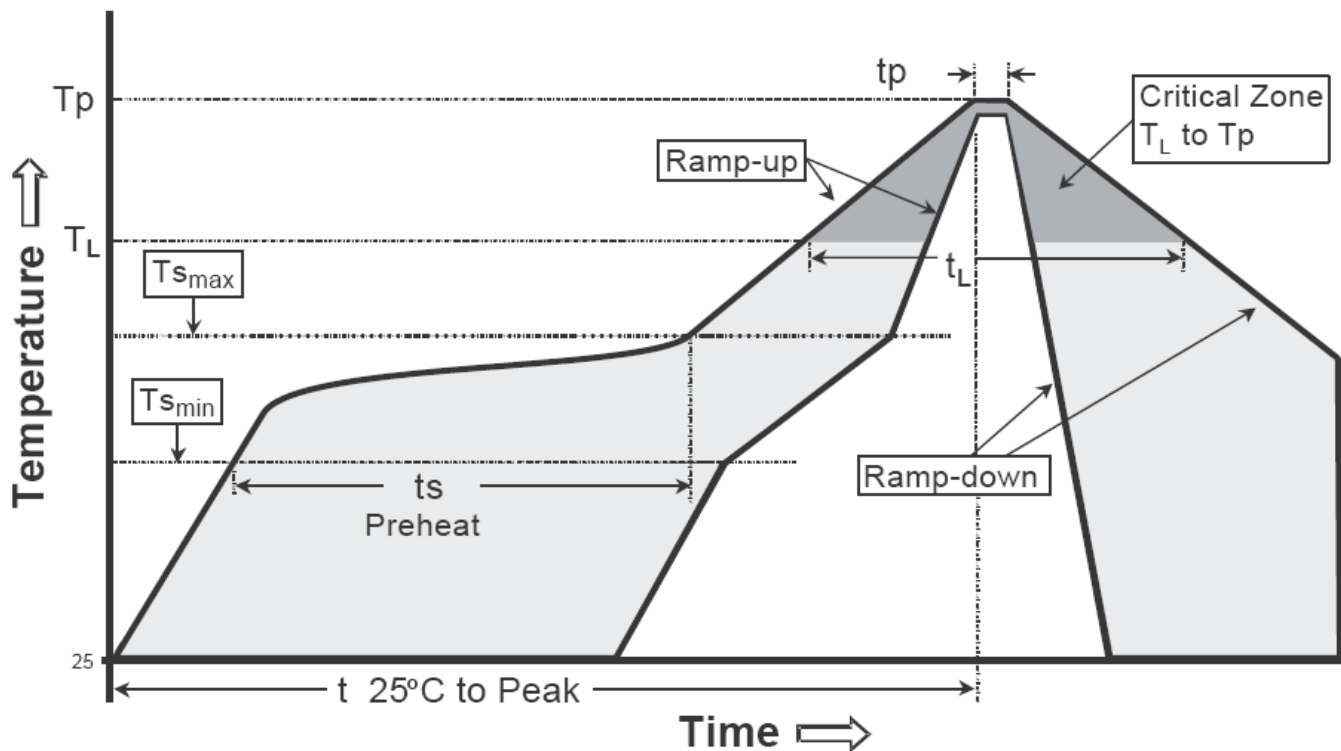
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

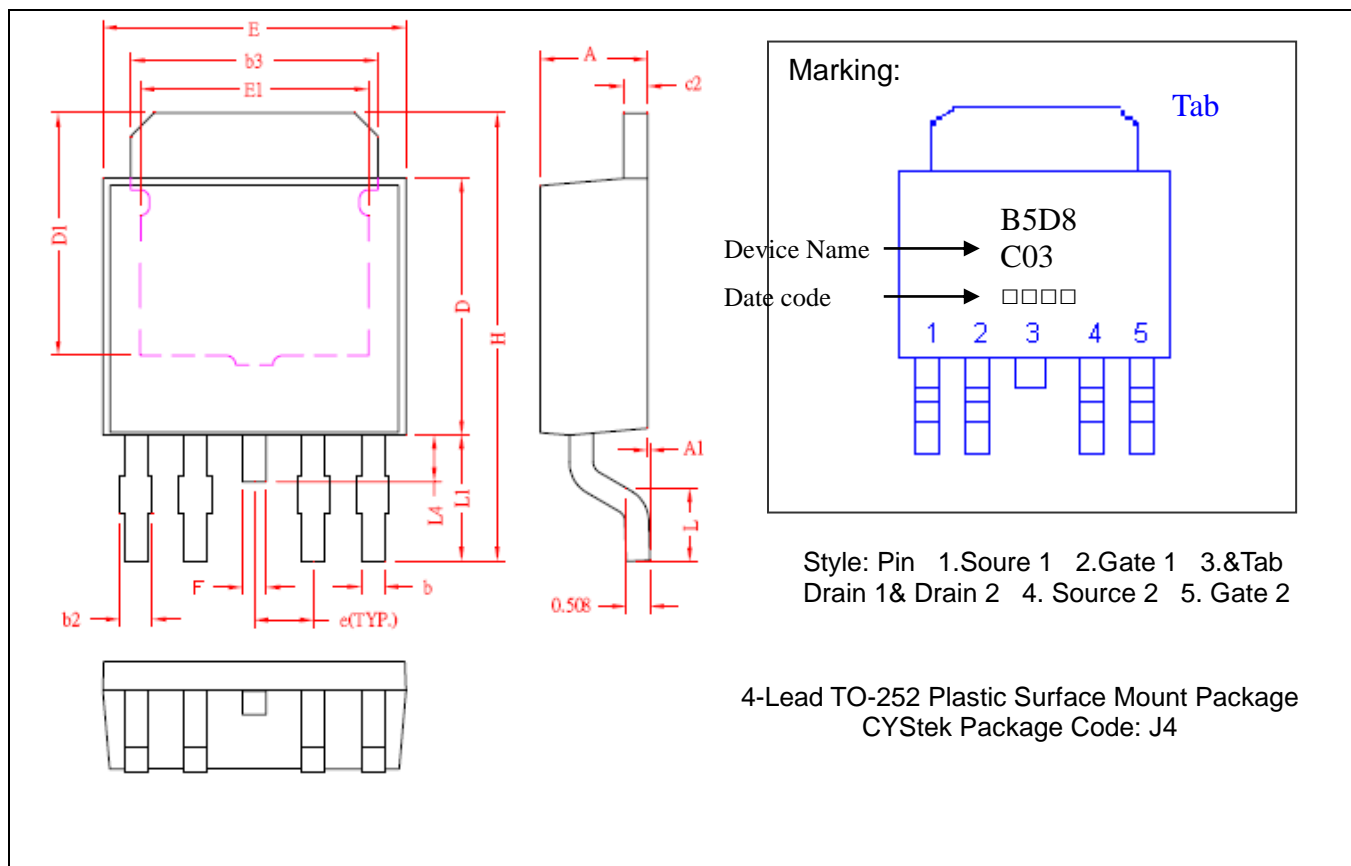
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-252-4L Dimension



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.0866	0.0945	2.20	2.40	E	0.2520	0.2677	6.40	6.80
A1	0.0000	0.0059	0.00	0.15	E1	0.1500	-	3.81	-
b	0.0157	0.0236	0.40	0.60	e	0.0500	REF	1.27	REF
b2	0.0199	0.0315	0.50	0.80	F	0.0157	0.0236	0.40	0.60
b3	0.2047	0.2165	5.20	5.50	H	0.3701	0.4016	9.40	10.20
c2	0.0177	0.0217	0.45	0.55	L	0.0551	0.0697	1.40	1.77
D	0.2126	0.2283	5.40	5.80	L1	0.0945	0.1181	2.40	3.00
D1	0.1799	-	4.57	-	L4	0.0315	0.0472	0.80	1.20

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead : Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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